Amplifier Transistors

NPN Silicon

Features

• These are Pb-Free Devices*



Rating	Symbol	Value	Unit
Collector - Emitter Voltage	V _{CEO}	50	Vdc
Collector - Base Voltage	V _{CBO}	60	Vdc
Emitter - Base Voltage	V _{EBO}	6.0	Vdc
Collector Current - Continuous	Ic	100	mAdc
Total Device Dissipation @ T _A = 25°C Derate above 25°C	PD	350 2.8	mW mW/°C
Total Device Dissipation @ T _C = 25°C Derate above 25°C	PD	1.0 8.0	W mW/°C
Operating and Storage Junction Temperature Range	T _J , T _{stg}	-55 to +150	°C

THERMAL CHARACTERISTICS

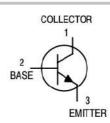
Characteristic	Symbol	Max	Unit	
Thermal Resistance, Junction-to-Ambient	R _{θJA}	357	°C/W	
Thermal Resistance, Junction-to-Case	R _{0JC}	125	°C/W	

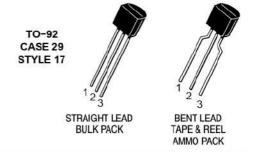
Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.



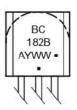
ON Semiconductor®

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MARKING DIAGRAM



A = Assembly Location

Y = Year WW = Work Week

= Pb-Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

Device	Package	Shipping [†]
BC182G	TO-92 (Pb-Free)	5000 Units / Bulk
BC182BG	TO-92 (Pb-Free)	5000 Units / Bulk
BC182BRL1G	TO-92 (Pb-Free)	2000 / Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

^{*}For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

ELECTRICAL CHARACTERISTICS ($T_A = 25^{\circ}\text{C}$ unless otherwise noted)

Characteristic	Symbol	Min	Тур	Max	Unit
OFF CHARACTERISTICS	12.0 M	-	d.	**	M ¹
Collector – Emitter Breakdown Voltage (I _C = 2.0 mA, I _B = 0)	V _{(BR)CEO}	50	<u> 178</u> 8.	-	٧
Collector –Base Breakdown Voltage (I _C = 10 μA, I _E = 0)	V _{(BR)CBO}	60	=	-	V
Emitter – Base Breakdown Voltage (I _E = 100 µA, I _C = 0)	V _{(BR)EBO}	6.0	-	-	٧
Collector Cutoff Current (V _{CB} = 50 V, V _{BE} = 0)	I _{CBO}	17.72	0.2	15	nA
Emitter-Base Leakage Current (V _{EB} = 4.0 V, I _C = 0)	I _{EBO}	i la	=	15	nA
ON CHARACTERISTICS					
DC Current Gain (I _C = 10 μA, V _{CE} = 5.0 V) BC	h _{FE}	40	==	_	8=
BC1	182 82B	120 180	=	500 500	
(I _C = 100 mA, V _{CE} = 5.0 V)	182	80	===	_	
Collector – Emitter On Voltage (I_C = 10 mA, I_B = 0.5 mA) (I_C = 100 mA, I_B = 5.0 mA) (Note 1)	V _{CE(sat)}	055 055	0.07 0.2	0.25 0.6	V
Base-Emitter Saturation Voltage ($I_C = 100 \text{ mA}, I_B = 5.0 \text{ mA}$) (Note 1)	V _{BE(sat)}	(1 10)	etrosi.	1.2	٧
Base–Emitter On Voltage (I_C = 100 μ A, V_{CE} = 5.0 V) (I_C = 2.0 mA, V_{CE} = 5.0 V) (I_C = 100 mA, V_{CE} = 5.0 V) (Note 1)	V _{BE(on)}	0.55 -	0.5 0.62 0.83	- 0.7 -	٧
DYNAMIC CHARACTERISTICS	1989		Ž.	*	d
Current - Gain — Bandwidth Product (I _C = 0.5 mA, V _{CE} = 3.0 V, f = 100 MHz) (I _C = 10 mA, V _{CE} = 5.0 V, f = 100 MHz)	ſΤ	- 150	100 200	_ _	MHz
Common Base Output Capacitance (V _{CB} = 10 V, I _C = 0, f = 1.0 MHz)	C _{ob}	-	=	5.0	pF
Common Base Input Capacitance (V _{EB} = 0.5 V, I _C = 0, f = 1.0 MHz)	C _{ib}	(4)	8.0	-	pF
	182 82B	125 240	=	500 500	UT3
Noise Figure (I _C = 0.2 mA, V_{CE} = 5.0 V, R_{S} = 2.0 k Ω , f = 1.0 kHz)	NF	<u> </u>	2.0	10	dB

^{1.} Pulse Test: Tp 300 s, Duty Cycle 2.0%.

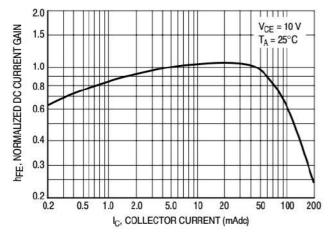


Figure 1. Normalized DC Current Gain

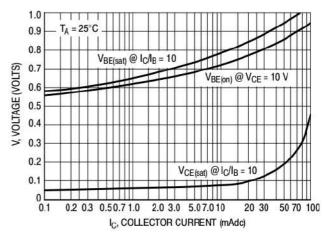


Figure 1. "Saturation" and "On" Voltages

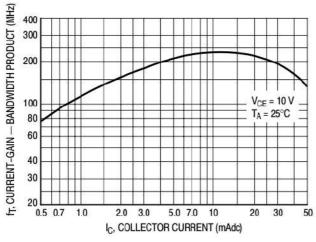


Figure 2. Current-Gain — Bandwidth Product

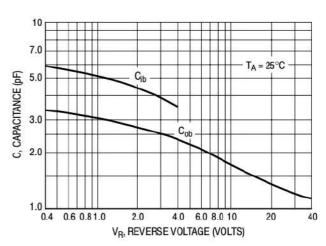


Figure 3. Capacitances

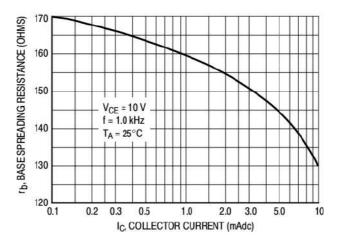
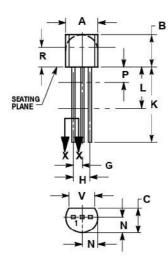


Figure 4. Base Spreading Resistance

PACKAGE DIMENSIONS

TO-92 (TO-226) CASE 29-11 ISSUE AM



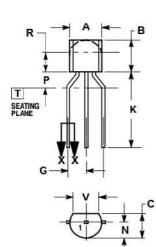
STRAIGHT LEAD **BULK PACK**



NOTES:

- DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
 CONTROLLING DIMENSION: INCH.
- CONTOUR OF PACKAGE BEYOND DIMENSION R IS UNCONTROLLED. LEAD DIMENSION IS UNCONTROLLED IN P AND
- BEYOND DIMENSION K MINIMUM.

- 1	INCHES		MILLIMETERS	
DIM	MIN	MAX	MIN	MAX
A	0.175	0.205	4.45	5.20
В	0.170	0.210	4.32	5.33
C	0.125	0.165	3.18	4.19
D	0.016	0.021	0.407	0.533
G	0.045	0.055	1.15	1.39
н	0.095	0.105	2.42	2.66
J	0.015	0.020	0.39	0.50
K	0.500		12.70	
L	0.250) .eee.	6.35	
N	0.080	0.105	2.04	2.66
Р		0.100		2.54
R	0.115		2.93	
V	0.135		3.43	222



BENTIFAD TAPE & REEL AMMO PACK



NOTES

- TES:
 DIMENSIONING AND TOLERANCING PER
 ASME Y14.5M, 1994.
 CONTROLLING DIMENSION: MILLIMETERS.
 CONTOUR OF PACKAGE BEYOND
 DIMENSION R IS UNCONTROLLED.

- LEAD DIMENSION IS UNCONTROLLED IN P AND BEYOND DIMENSION K MINIMUM.

	MILLIMETERS		
DIM	MIN	MAX	
Α	4.45	5.20	
В	4.32	5.33	
C	3.18	4.19	
D	0.40	0.54	
G	2.40	2.80	
J	0.39	0.50	
K	12.70		
N	2.04	2.66	
P	1.50	4.00	
R	2.93		
V	3.43		

STYLE 17:

COLLECTOR PIN 1.

2. BASE EMITTER

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